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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	PowerPC e300c2
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	333MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC 2.2
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (3)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography
Package / Case	516-BBGA
Supplier Device Package	516-PBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8321ecvrafdca

NOTE

The QUICC Engine block can also support a UTOPIA level 2 capable of supporting 31 multi-PHY (MPC8323E- and MPC8323-specific).

The MPC8323E security engine (SEC 2.2) allows CPU-intensive cryptographic operations to be offloaded from the main CPU core. The security-processing accelerator provides hardware acceleration for the DES, 3DES, AES, SHA-1, and MD-5 algorithms.

In summary, the MPC8323E family provides users with a highly integrated, fully programmable communications processor. This helps ensure that a low-cost system solution can be quickly developed and offers flexibility to accommodate new standards and evolving system requirements.

1.1 MPC8323E Features

Major features of the MPC8323E are as follows:

- High-performance, low-power, and cost-effective single-chip data-plane/control-plane solution for ATM or IP/Ethernet packet processing (or both).
- MPC8323E QUICC Engine block offers a future-proof solution for next generation designs by supporting programmable protocol termination and network interface termination to meet evolving protocol standards.
- Single platform architecture supports the convergence of IP packet networks and ATM networks.
- DDR1/DDR2 memory controller—one 32-bit interface at up to 266 MHz supporting both DDR1 and DDR2.
- An e300c2 core built on Power Architecture technology with 16-Kbyte instruction and data caches, and dual integer units.
- Peripheral interfaces such as 32-bit PCI (2.2) interface up to 66-MHz operation, 16-bit local bus interface up to 66-MHz operation, and USB 2.0 (full-/low-speed).
- Security engine provides acceleration for control and data plane security protocols.
- High degree of software compatibility with previous-generation PowerQUICC processor-based designs for backward compatibility and easier software migration.

1.1.1 Protocols

The protocols are as follows:

- ATM SAR up to 155 Mbps (OC-3) full duplex, with ATM traffic shaping (ATF TM4.1)
- Support for ATM AAL1 structured and unstructured circuit emulation service (CES 2.0)
- Support for IMA and ATM transmission convergence sub-layer
- ATM OAM handling features compatible with ITU-T I.610
- IP termination support for IPv4 and IPv6 packets including TOS, TTL, and header checksum processing
- Extensive support for ATM statistics and Ethernet RMON/MIB statistics
- Support for 64 channels of HDLC/transparent

Table 7. CLKIN DC Electrical Characteristics (continued)

CLKIN input current	$0 V \le V_{IN} \le OV_{DD}$	I_{IN}	—	±5	μA
PCI_SYNC_IN input current	$0 V \le V_{IN} \le 0.5 V$ or $OV_{DD} - 0.5 V \le V_{IN} \le OV_{DD}$	I_{IN}	—	±5	μA
PCI_SYNC_IN input current	$0.5 V \le V_{IN} \le OV_{DD} - 0.5 V$	I_{IN}	—	±50	μA

4.2 AC Electrical Characteristics

The primary clock source for the MPC8323E can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. Table 8 provides the clock input (CLKIN/PCI_CLK) AC timing specifications for the MPC8323E.

Table 8. CLKIN AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
CLKIN/PCI_CLK frequency	f_{CLKIN}	25	—	66.67	MHz	1
CLKIN/PCI_CLK cycle time	t_{CLKIN}	15	—	—	ns	—
CLKIN rise and fall time	t_{KH}, t_{KL}	0.6	0.8	4	ns	2
PCI_CLK rise and fall time	t_{PCH}, t_{PCL}	0.6	0.8	1.2	ns	2
CLKIN/PCI_CLK duty cycle	t_{KHK}/t_{CLKIN}	40	—	60	%	3
CLKIN/PCI_CLK jitter	—	—	—	±150	ps	4, 5

Notes:
1. **Caution:** The system, core, security, and QUICC Engine block must not exceed their respective maximum or minimum operating frequencies.
2. Rise and fall times for CLKIN/PCI_CLK are measured at 0.4 and 2.7 V.
3. Timing is guaranteed by design and characterization.
4. This represents the total input jitter—short term and long term—and is guaranteed by design.
5. The CLKIN/PCI_CLK driver's closed loop jitter bandwidth should be < 500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track CLKIN drivers with the specified jitter.

5 RESET Initialization

This section describes the AC electrical specifications for the reset initialization timing requirements of the MPC8323E. Table 9 provides the reset initialization AC timing specifications for the reset component(s).

Table 9. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$ or $\overline{\text{SRESET}}$ (input) to activate reset flow	32	—	$t_{PCI\_SYNC\_IN}$	1
Required assertion time of $\overline{\text{PORESET}}$ with stable clock applied to CLKIN when the MPC8323E is in PCI host mode	32	—	t_{CLKIN}	2
Required assertion time of $\overline{\text{PORESET}}$ with stable clock applied to PCI_SYNC_IN when the MPC8323E is in PCI agent mode	32	—	$t_{PCI\_SYNC\_IN}$	1

Table 13. DDR2 SDRAM Capacitance for D*n*_GV$_{DD}$(typ) = 1.8 V

Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. D*n*_GV$_{DD}$ = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25 °C, V_{OUT} = D*n*_GV$_{DD}$ ÷ 2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 14 provides the recommended operating conditions for the DDR1 SDRAM component(s) of the MPC8323E when D*n*_GV$_{DD}$(typ) = 2.5 V.

Table 14. DDR1 SDRAM DC Electrical Characteristics for D*n*_GV$_{DD}$(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	D*n*_GV$_{DD}$	2.375	2.625	V	1
I/O reference voltage	MVREF*n*$_{REF}$	0.49 × D*n*_GV$_{DD}$	0.51 × D*n*_GV$_{DD}$	V	2
I/O termination voltage	V_{TT}	MVREF*n*$_{REF}$ – 0.04	MVREF*n*$_{REF}$ + 0.04	V	3
Input high voltage	V_{IH}	MVREF*n*$_{REF}$ + 0.15	D*n*_GV$_{DD}$ + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MVREF*n*$_{REF}$ – 0.15	V	—
Output leakage current	I_{OZ}	–9.9	–9.9	µA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–16.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	16.2	—	mA	—

Notes:
1. D*n*_GV$_{DD}$ is expected to be within 50 mV of the DRAM D*n*_GV$_{DD}$ at all times.
2. MVREF*n*$_{REF}$ is expected to be equal to 0.5 × D*n*_GV$_{DD}$, and to track D*n*_GV$_{DD}$ DC variations as measured at the receiver. Peak-to-peak noise on MVREF*n*$_{REF}$ may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MVREF*n*$_{REF}$. This rail should track variations in the DC level of MVREF*n*$_{REF}$.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ D*n*_GV$_{DD}$.

Table 15 provides the DDR1 capacitance D*n*_GV$_{DD}$(typ) = 2.5 V.

Table 15. DDR1 SDRAM Capacitance for D*n*_GV$_{DD}$(typ) = 2.5 V Interface

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ,DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. D*n*_GV$_{DD}$ = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25° C, V_{OUT} = D*n*_GV$_{DD}$ ÷ 2, V_{OUT} (peak-to-peak) = 0.2 V.

6.2 DDR1 and DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR1 and DDR2 SDRAM interface.

6.2.1 DDR1 and DDR2 SDRAM Input AC Timing Specifications

Table 16 provides the input AC timing specifications for the DDR2 SDRAM (D*n*_GV_{DD}(typ) = 1.8 V).

Table 16. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions with D*n*_GV_{DD} of 1.8 ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MVREFn_{REF} – 0.25	V	—
AC input high voltage	V_{IH}	MVREFn_{REF} + 0.25	—	V	—

Table 17 provides the input AC timing specifications for the DDR1 SDRAM (D*n*_GV_{DD}(typ) = 2.5 V).

Table 17. DDR1 SDRAM Input AC Timing Specifications for 2.5 V Interface

At recommended operating conditions with D*n*_GV_{DD} of 2.5 ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MVREFn_{REF} – 0.31	V	—
AC input high voltage	V_{IH}	MVREFn_{REF} + 0.31	—	V	—

Table 18 provides the input AC timing specifications for the DDR1 and DDR2 SDRAM interface.

Table 18. DDR1 and DDR2 SDRAM Input AC Timing Specifications

At recommended operating conditions with D*n*_GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
Controller skew for MDQS—MDQ/MDM	t_{CISKEW}			ps	1, 2
266 MHz		–750	750		
200 MHz		–1250	1250		

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that is captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the following equation: $t_{DISKEW} = \pm(T/4 - abs(t_{CISKEW}))$ where T is the clock period and $abs(t_{CISKEW})$ is the absolute value of t_{CISKEW}.

Table 26. RMII Receive AC Timing Specifications (continued)

At recommended operating conditions with OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit
REF_CLK clock fall time V_{IH}(max) to V_{IL}(min)	t_{RMXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first three letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{RMRDVKH}$ symbolizes RMII receive timing (RMR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{RMX} clock reference (K) going to the high (H) state or setup time. Also, $t_{RMRDXKL}$ symbolizes RMII receive timing (RMR) with respect to the time data input signals (D) went invalid (X) relative to the t_{RMX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII (RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 11 provides the AC test load.

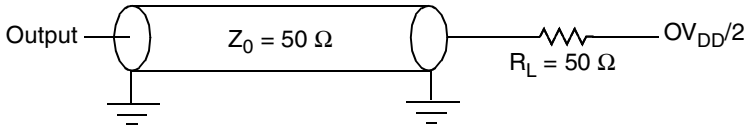

Figure 11. AC Test Load

Figure 12 shows the RMII receive AC timing diagram.

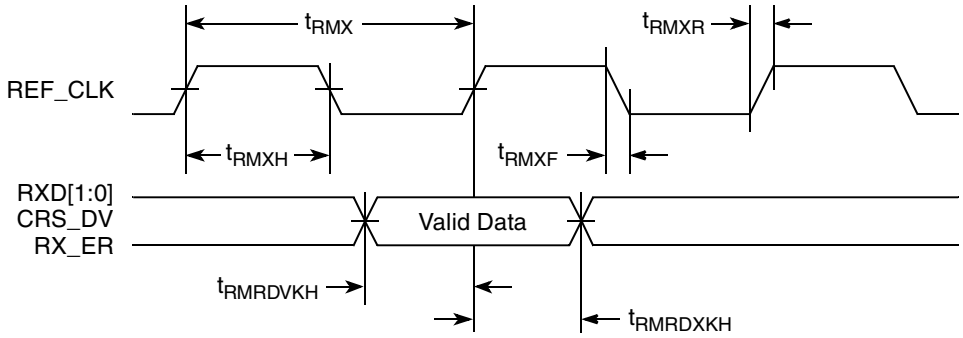

Figure 12. RMII Receive AC Timing Diagram

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for MII, and RMII are specified in Section 8.1, “Ethernet Controller (10/100 Mbps)—MII/RMII Electrical Characteristics.”

8.3.1 MII Management DC Electrical Characteristics

MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in Table 27.

Table 27. MII Management DC Electrical Characteristics When Powered at 3.3 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	—		2.97	3.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	OV_{DD} = Min	2.10	OV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	OV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—		2.00	—	V
Input low voltage	V_{IL}	—		—	0.80	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$		—	±5	μA

8.3.2 MII Management AC Electrical Specifications

Table 28 provides the MII management AC timing specifications.

Table 28. MII Management AC Timing Specifications

At recommended operating conditions with OV_{DD} is 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit	Notes
MDC frequency	f_{MDC}	—	2.5	—	MHz	—
MDC period	t_{MDC}	—	400	—	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—
MDC to MDIO delay	t_{MDKHDX}	10	—	70	ns	—
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	—
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	—
MDC fall time	t_{MDHF}	—	—	10	ns	—

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 13 shows the MII management AC timing diagram.

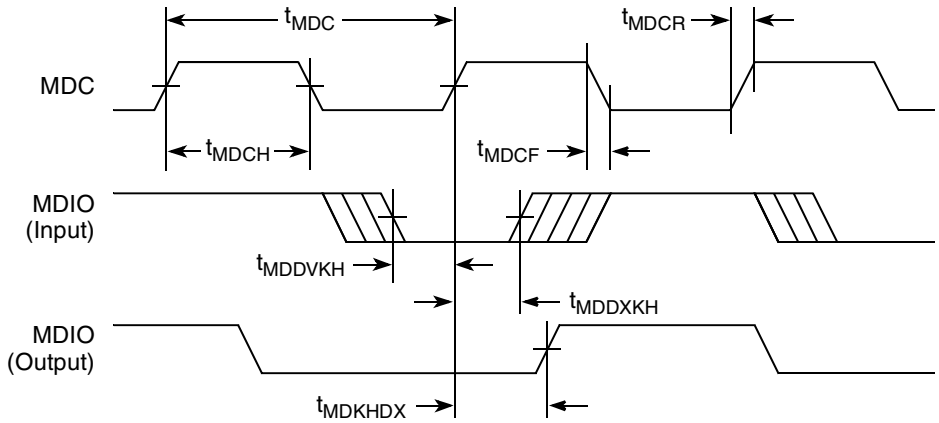

Figure 13. MII Management Interface Timing Diagram

9 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8323E.

9.1 Local Bus DC Electrical Characteristics

Table 29 provides the DC electrical characteristics for the local bus interface.

Table 29. Local Bus DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
High-level output voltage, I_{OH} = –100 µA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 µA	V_{OL}	—	0.2	V
Input current	I_{IN}	—	±5	µA

9.2 Local Bus AC Electrical Specifications

Table 30 describes the general timing parameters of the local bus interface of the MPC8323E.

Table 30. Local Bus General Timing Parameters

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	15	—	ns	2
Input setup to local bus clock (LCLK*n*)	t_{LBIVKH}	7	—	ns	3, 4
Input hold from local bus clock (LCLK*n*)	t_{LBIXKH}	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT1}$	1.5	—	ns	5

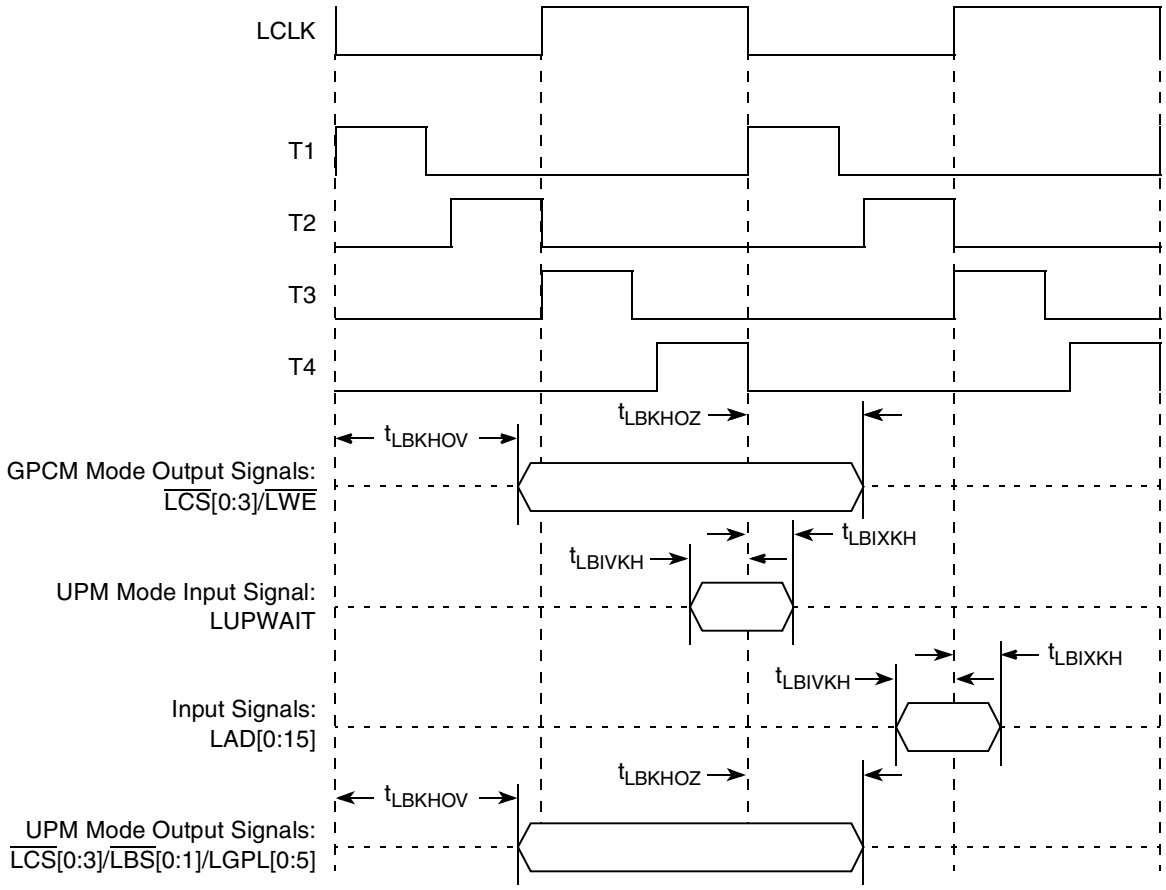

Figure 17. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 4

10 JTAG

This section describes the DC and AC electrical specifications for the IEEE Std. 1149.1™ (JTAG) interface of the MPC8323E.

10.1 JTAG DC Electrical Characteristics

Table 31 provides the DC electrical characteristics for the IEEE Std. 1149.1 (JTAG) interface of the MPC8323E.

Table 31. JTAG Interface DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V
Input high voltage	V_{IH}	—	2.5	OV_{DD} + 0.3	V

Table 32. JTAG AC Timing Specifications (Independent of CLKIN)[1] (continued)

At recommended operating conditions (see Table 2).

Parameter	Symbol[2]	Min	Max	Unit	Notes
JTAG external clock to output high impedance: Boundary-scan data TDO	 t_{JTKLDZ} t_{JTKLOZ}	 2 2	 19 9	ns	 5, 6 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 14). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.
6. Guaranteed by design and characterization.

Figure 18 provides the AC test load for TDO and the boundary-scan outputs of the MPC8323E.

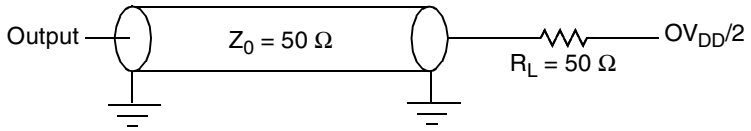

Figure 18. AC Test Load for the JTAG Interface

Figure 19 provides the JTAG clock input timing diagram.

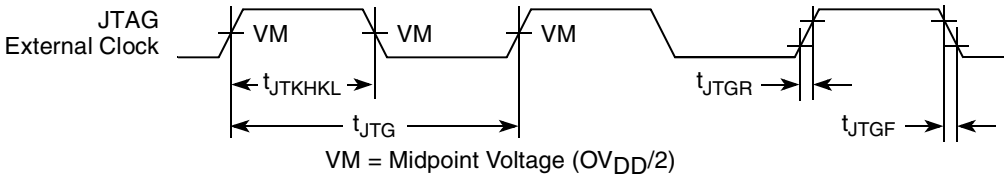

Figure 19. JTAG Clock Input Timing Diagram

Figure 20 provides the $\overline{\text{TRST}}$ timing diagram.

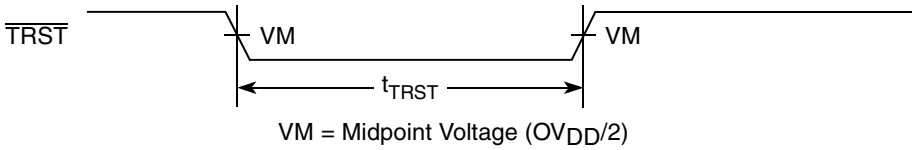

Figure 20. $\overline{\text{TRST}}$ Timing Diagram

Table 34. I²C AC Electrical Specifications (continued)

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 33).

Parameter	Symbol[1]	Min	Max	Unit
Rise time of both SDA and SCL signals	t_{I2CR}	20 + 0.1 C_b[4]	300	ns
Fall time of both SDA and SCL signals	t_{I2CF}	20 + 0.1 C_b[4]	300	ns
Setup time for STOP condition	t_{I2PVKH}	0.6	—	µs
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	µs
Noise margin at the LOW level for each connected device (including hysteresis)	V_{NL}	0.1 × OV_{DD}	—	V
Noise margin at the HIGH level for each connected device (including hysteresis)	V_{NH}	0.2 × OV_{DD}	—	V

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{I2DVKH} symbolizes I²C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I²C timing (I2) for the time that the data with respect to the start condition (S) went invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I²C timing (I2) for the time that the data with respect to the stop condition (P) reaching the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. MPC8323E provides a hold time of at least 300 ns for the SDA signal (referred to the V_{IH}(min) of the SCL signal) to bridge the undefined region of the falling edge of SCL.
3. The maximum t_{I2DVKH} has only to be met if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
4. C_B = capacitance of one bus line in pF.

Figure 23 provides the AC test load for the I²C.

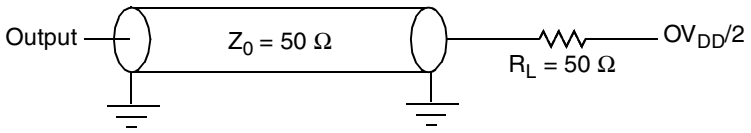

Figure 23. I²C AC Test Load

Figure 24 shows the AC timing diagram for the I²C bus.

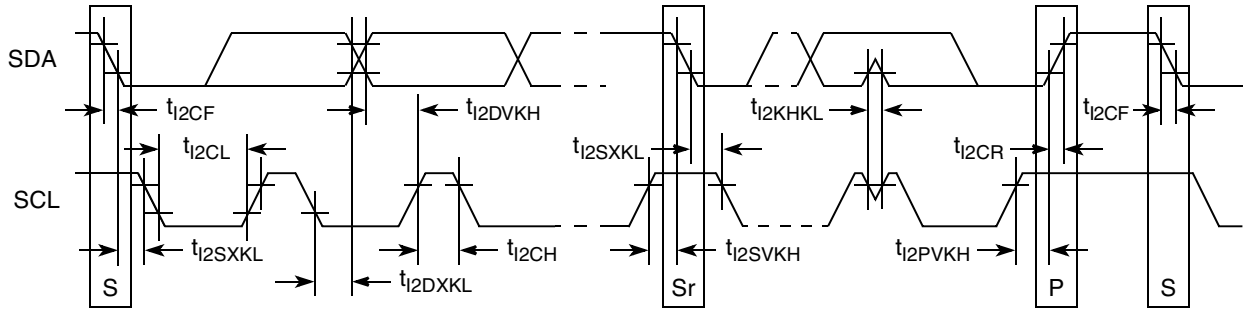

Figure 24. I²C Bus AC Timing Diagram

18 UTOPIA

This section describes the UTOPIA DC and AC electrical specifications of the MPC8323E.

NOTE

The MPC8321E and MPC8321 do not support UTOPIA.

18.1 UTOPIA DC Electrical Characteristics

Table 48 provides the DC electrical characteristics for the MPC8323E UTOPIA.

Table 48. UTOPIA DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V ≤ V_{IN} ≤ OV_{DD}	—	±5	μA

18.2 UTOPIA AC Timing Specifications

Table 49 provides the UTOPIA input and output AC timing specifications.

Table 49. UTOPIA AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
UTOPIA outputs—Internal clock delay	t_{UIKHOV}	0	5.5	ns
UTOPIA outputs—External clock delay	t_{UEKHOV}	1	8	ns
UTOPIA outputs—Internal clock high impedance	t_{UIKHOX}	0	5.5	ns
UTOPIA outputs—External clock high impedance	t_{UEKHOX}	1	8	ns
UTOPIA inputs—Internal clock input setup time	t_{UIIVKH}	8	—	ns
UTOPIA inputs—External clock input setup time	t_{UEIVKH}	4	—	ns
UTOPIA inputs—Internal clock input hold time	t_{UIIXKH}	0	—	ns
UTOPIA inputs—External clock input hold time	t_{UEIXKH}	1	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{UIKHOX} symbolizes the UTOPIA outputs internal timing (UI) for the time t_{UTOPIA} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

21 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8323E is available in a thermally enhanced Plastic Ball Grid Array (PBGA); see Section 21.1, "Package Parameters for the MPC8323E PBGA," and Section 21.2, "Mechanical Dimensions of the MPC8323E PBGA," for information on the PBGA.

21.1 Package Parameters for the MPC8323E PBGA

The package parameters are as provided in the following list. The package type is 27 mm × 27 mm, 516 PBGA.

Package outline	27 mm × 27 mm
Interconnects	516
Pitch	1.00 mm
Module height (typical)	2.25 mm
Solder Balls	62 Sn/36 Pb/2 Ag (ZQ package) 95.5 Sn/0.5 Cu/4Ag (VR package)
Ball diameter (typical)	0.6 mm

21.2 Mechanical Dimensions of the MPC8323E PBGA

Figure 42 shows the mechanical dimensions and bottom surface nomenclature of the MPC8323E, 516-PBGA package.

21.3 Pinout Listings

Table 55 shows the pin list of the MPC8323E.

Table 55. MPC8323E PBGA Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
DDR Memory Controller Interface				
MEMC_MDQ0	AE9	IO	GV_{DD}	—
MEMC_MDQ1	AD10	IO	GV_{DD}	—
MEMC_MDQ2	AF10	IO	GV_{DD}	—
MEMC_MDQ3	AF9	IO	GV_{DD}	—
MEMC_MDQ4	AF7	IO	GV_{DD}	—
MEMC_MDQ5	AE10	IO	GV_{DD}	—
MEMC_MDQ6	AD9	IO	GV_{DD}	—
MEMC_MDQ7	AF8	IO	GV_{DD}	—
MEMC_MDQ8	AE6	IO	GV_{DD}	—
MEMC_MDQ9	AD7	IO	GV_{DD}	—
MEMC_MDQ10	AF6	IO	GV_{DD}	—
MEMC_MDQ11	AC7	IO	GV_{DD}	—
MEMC_MDQ12	AD8	IO	GV_{DD}	—
MEMC_MDQ13	AE7	IO	GV_{DD}	—
MEMC_MDQ14	AD6	IO	GV_{DD}	—
MEMC_MDQ15	AF5	IO	GV_{DD}	—
MEMC_MDQ16	AD18	IO	GV_{DD}	—
MEMC_MDQ17	AE19	IO	GV_{DD}	—
MEMC_MDQ18	AF17	IO	GV_{DD}	—
MEMC_MDQ19	AF19	IO	GV_{DD}	—
MEMC_MDQ20	AF18	IO	GV_{DD}	—
MEMC_MDQ21	AE18	IO	GV_{DD}	—
MEMC_MDQ22	AF20	IO	GV_{DD}	—
MEMC_MDQ23	AD19	IO	GV_{DD}	—
MEMC_MDQ24	AD21	IO	GV_{DD}	—
MEMC_MDQ25	AF22	IO	GV_{DD}	—
MEMC_MDQ26	AC21	IO	GV_{DD}	—
MEMC_MDQ27	AF21	IO	GV_{DD}	—
MEMC_MDQ28	AE21	IO	GV_{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Power and Ground Supplies				
$AV_{DD}1$	P3	I	$AV_{DD}1$	—
$AV_{DD}2$	AA1	I	$AV_{DD}2$	—
$AV_{DD}3$	AB15	I	$AV_{DD}3$	—
$AV_{DD}4$	C24	I	$AV_{DD}4$	—
MVREF1	AB8	I	DDR reference voltage	—
MVREF2	AB17	I	DDR reference voltage	—
PCI				
$\overline{\text{PCI\_INTA}}$ /$\overline{\text{IRQ\_OUT}}$	AF2	O	OV_{DD}	2
$\overline{\text{PCI\_RESET\_OUT}}$	AE2	O	OV_{DD}	—
PCI_AD0/MSRCID0 (DDR ID)	L1	IO	OV_{DD}	—
PCI_AD1/MSRCID1 (DDR ID)	L2	IO	OV_{DD}	—
PCI_AD2/MSRCID2 (DDR ID)	M1	IO	OV_{DD}	—
PCI_AD3/MSRCID3 (DDR ID)	M2	IO	OV_{DD}	—
PCI_AD4/MSRCID4 (DDR ID)	L3	IO	OV_{DD}	—
PCI_AD5/MDVAL (DDR ID)	N1	IO	OV_{DD}	—
PCI_AD6	N2	IO	OV_{DD}	—
PCI_AD7	M3	IO	OV_{DD}	—
PCI_AD8	P1	IO	OV_{DD}	—
PCI_AD9	R1	IO	OV_{DD}	—
PCI_AD10	N3	IO	OV_{DD}	—
PCI_AD11	N4	IO	OV_{DD}	—
PCI_AD12	T1	IO	OV_{DD}	—
PCI_AD13	R2	IO	OV_{DD}	—
PCI_AD14/ECID_TMODE_IN	T2	IO	OV_{DD}	—
PCI_AD15	U1	IO	OV_{DD}	—
PCI_AD16	Y2	IO	OV_{DD}	—
PCI_AD17	Y1	IO	OV_{DD}	—
PCI_AD18	AA2	IO	OV_{DD}	—
PCI_AD19	AB1	IO	OV_{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
CE/GPIO				
GPIO_PA0/SER1_TXD[0]/TDMA_TXD[0]/USBTXN	G3	IO	OV_{DD}	—
GPIO_PA1/SER1_TXD[1]/TDMA_TXD[1]/USBTXP	F3	IO	OV_{DD}	—
GPIO_PA2/SER1_TXD[2]/TDMA_TXD[2]	F2	IO	OV_{DD}	—
GPIO_PA3/SER1_TXD[3]/TDMA_TXD[3]	E3	IO	OV_{DD}	—
GPIO_PA4/SER1_RXD[0]/TDMA_RXD[0]/USBRXP	E2	IO	OV_{DD}	—
GPIO_PA5/SER1_RXD[1]/TDMA_RXD[1]/USBRXN	E1	IO	OV_{DD}	—
GPIO_PA6/SER1_RXD[2]/TDMA_RXD[2]/USBRXD	D3	IO	OV_{DD}	—
GPIO_PA7/SER1_RXD[3]/TDMA_RXD[3]	D2	IO	OV_{DD}	—
GPIO_PA8/SER1_CD/TDMA_REQ/$\overline{\text{USBOE}}$	D1	IO	OV_{DD}	—
GPIO_PA9 TDMA_CLKO	C3	IO	OV_{DD}	—
GPIO_PA10/SER1_CTS/TDMA_RSYNC	C2	IO	OV_{DD}	—
GPIO_PA11/TDMA_STROBE	C1	IO	OV_{DD}	—
GPIO_PA12/SER1_RTS/TDMA_TSYNC	B1	IO	OV_{DD}	—
GPIO_PA13/CLK9/BRGO9	H4	IO	OV_{DD}	—
GPIO_PA14/CLK11/BRGO10	G4	IO	OV_{DD}	—
GPIO_PA15/BRGO7	J4	IO	OV_{DD}	—
GPIO_PA16/ LA0 (LBIU)	K24	IO	OV_{DD}	—
GPIO_PA17/ LA1 (LBIU)	K26	IO	OV_{DD}	—
GPIO_PA18/Enet2_TXD[0]/SER2_TXD[0]/ TDMB_TXD[0]/LA2 (LBIU)	G25	IO	OV_{DD}	—
GPIO_PA19/Enet2_TXD[1]/SER2_TXD[1]/ TDMB_TXD[1]/LA3 (LBIU)	G26	IO	OV_{DD}	—
GPIO_PA20/Enet2_TXD[2]/SER2_TXD[2]/ TDMB_TXD[2]/LA4 (LBIU)	H25	IO	OV_{DD}	—
GPIO_PA21/Enet2_TXD[3]/SER2_TXD[3]/ TDMB_TXD[3]/LA5 (LBIU)	H26	IO	OV_{DD}	—
GPIO_PA22/Enet2_RXD[0]/SER2_RXD[0]/ TDMB_RXD[0]/LA6 (LBIU)	C25	IO	OV_{DD}	—
GPIO_PA23/Enet2_RXD[1]/SER2_RXD[1]/ TDMB_RXD[1]/LA7 (LBIU)	C26	IO	OV_{DD}	—
GPIO_PA24/Enet2_RXD[2]/SER2_RXD[2]/ TDMB_RXD[2]/LA8 (LBIU)	D25	IO	OV_{DD}	—
GPIO_PA25/Enet2_RXD[3]/SER2_RXD[3]/ TDMB_RXD[3]/LA9 (LBIU)	D26	IO	OV_{DD}	—

Table 57. Operating Frequencies for PBGA (continued)

Characteristic[1]	Max Operating Frequency	Unit
DDR1/DDR2 memory bus frequency (MCLK)[2]	133	MHz
Local bus frequency (LCLK*n*)[3]	66	MHz
PCI input frequency (CLKIN or PCI_CLK)	66	MHz

1 The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen such that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies.
2 The DDR1/DDR2 data rate is 2× the DDR1/DDR2 memory bus frequency.
3 The local bus frequency is 1/2, 1/4, or 1/8 of the *lb_clk* frequency (depending on LCRR[CLKDIV]) which is in turn 1× or 2× the *csb_clk* frequency (depending on RCWL[LBCM]).

22.4 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] parameter. Table 58 shows the multiplication factor encodings for the system PLL.

NOTE

System PLL VCO frequency = 2 × (CSB frequency) × (System PLL VCO divider).

The VCO divider needs to be set properly so that the System PLL VCO frequency is in the range of 300–600 MHz.

Table 58. System PLL Multiplication Factors

RCWL[SPMF]	System PLL Multiplication Factor
0000	Reserved
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6
0111–1111	Reserved

As described in Section 22, “Clocking,” the LBCM, DDRCM, and SPMF parameters in the reset configuration word low and the $\overline{\text{CFG\_CLKIN\_DIV}}$ configuration input signal select the ratio between the primary clock input (CLKIN or PCI_CLK) and the internal coherent system bus clock (*csb_clk*). Table 59

22.7 Suggested PLL Configurations

To simplify the PLL configurations, the MPC8323E might be separated into two clock domains. The first domain contain the CSB PLL and the core PLL. The core PLL is connected serially to the CSB PLL, and has the csb_clk as its input clock. The second clock domain has the QUICC Engine PLL. The clock domains are independent, and each of their PLLs are configured separately. Both of the domains has one common input clock. Table 63 shows suggested PLL configurations for 33, 25, and 66 MHz input clocks.

Table 63. Suggested PLL Configurations

Conf No.	SPMF	Core PLL	CEMF	CEDF	Input Clock Frequency (MHz)	CSB Frequency (MHz)	Core Frequency (MHz)	QUICC Engine Frequency (MHz)
1	0100	0000100	0110	0	33.33	133.33	266.66	200
2	0100	0000101	1000	0	25	100	250	200
3	0010	0000100	0011	0	66.67	133.33	266.66	200
4	0100	0000101	0110	0	33.33	133.33	333.33	200
5	0101	0000101	1000	0	25	125	312.5	200
6	0010	0000101	0011	0	66.67	133.33	333.33	200

23 Thermal

This section describes the thermal specifications of the MPC8323E.

23.1 Thermal Characteristics

Table 64 provides the package thermal characteristics for the 516 27×27 mm PBGA of the MPC8323E.

Table 64. Package Thermal Characteristics for PBGA

Characteristic	Board type	Symbol	Value	Unit	Notes
Junction-to-ambient natural convection	Single-layer board (1s)	$R_{\theta JA}$	28	°C/W	1, 2
Junction-to-ambient natural convection	Four-layer board (2s2p)	$R_{\theta JA}$	21	°C/W	1, 2, 3
Junction-to-ambient (@200 ft/min)	Single-layer board (1s)	$R_{\theta JMA}$	23	°C/W	1, 3
Junction-to-ambient (@200 ft/min)	Four-layer board (2s2p)	$R_{\theta JMA}$	18	°C/W	1, 3
Junction-to-board	—	$R_{\theta JB}$	13	°C/W	4
Junction-to-case	—	$R_{\theta JC}$	9	°C/W	5

output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

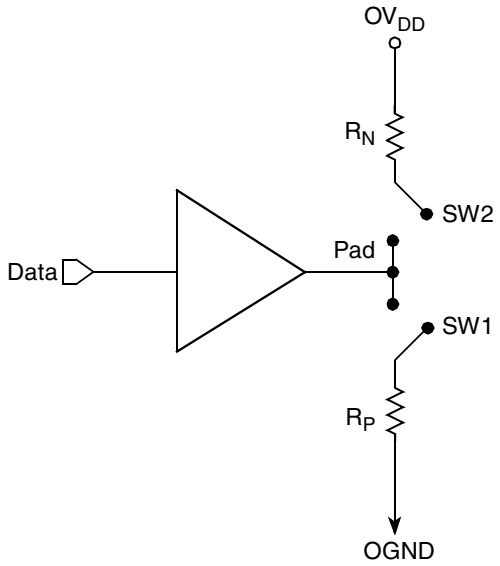

Figure 45. Driver Impedance Measurement

The value of this resistance and the strength of the driver's current source can be found by making two measurements. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{source} \times I_{source}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term}. The measured voltage is $V_2 = (1/(1/R_1 + 1/R_2)) \times I_{source}$. Solving for the output impedance gives $R_{source} = R_{term} \times (V_1/V_2 - 1)$. The drive current is then $I_{source} = V_1/R_{source}$.

Table 65 summarizes the signal impedance targets. The driver impedance are targeted at minimum V_{DD}, nominal OV_{DD}, 105°C.

Table 65. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI	DDR DRAM	Symbol	Unit
R_N	42 Target	25 Target	20 Target	Z_0	W
R_P	42 Target	25 Target	20 Target	Z_0	W
Differential	NA	NA	NA	Z_{DIFF}	W

Note: Nominal supply voltages. See Table 1, T_j = 105°C.

24.6 Configuration Pin Multiplexing

The MPC8323E provides the user with power-on configuration options which can be set through the use of external pull-up or pull-down resistors of 4.7 kΩ on certain output pins (see customer visible configuration pins). These pins are generally used as output only pins in normal operation.

Table 67. Document Revision History

Rev. No.	Date	Substantive Change(s)
2	4/2008	• Removed Figures 2 and 3 overshoot and undershoot voltage specs from Section 2.1.2, "Power Supply Voltage Specification," and footnotes 4 and 5 from Table 1. • Corrected QUIESCE signal to be an output signal in Table 55. • Added column for GVDD (1.8 V) - DDR2 - to Table 6 with 0.212-W typical power dissipation. • Added Figure 4 DDR input timing diagram. • Removed CE_TRB* and CE_PIO* signals from Table 55. • Added three local bus AC specifications to Table 30 (duty cycle, jitter, delay between input clock and local bus clock). • Added row in Table 2 stating junction temperature range of 0 to 105•C. • Modified Section 2.2, "Power Sequencing," to include $\overline{\text{PORESET}}$ requirement.
1	6/2007	Correction to descriptive text in Section 2.2.
0	6/2007	Initial release.

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Document Number: MPC8323EEC
Rev. 4
09/2010